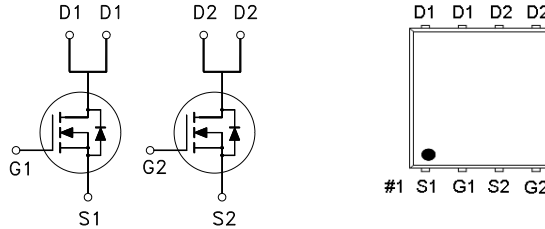


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D^3
30V	19mΩ	21A



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current ³	$T_C = 25\text{ }^\circ\text{C}$	I_D	21	A
	$T_C = 100\text{ }^\circ\text{C}$		13	
	$T_A = 25\text{ }^\circ\text{C}$		7.5	
	$T_A = 70\text{ }^\circ\text{C}$		6	
Pulsed Drain Current ¹		I_{DM}	25	
Avalanche Current		I_{AS}	17	
Avalanche Energy	L = 0.1mH	E_{AS}	15	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	14	W
	$T_C = 100\text{ }^\circ\text{C}$		5	
	$T_A = 25\text{ }^\circ\text{C}$		1.7	
	$T_A = 70\text{ }^\circ\text{C}$		1.1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		70	°C / W
Junction-to-Case	$R_{\theta JC}$		8.5	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ }^\circ\text{C}$.

³Package limitation current is 9A.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

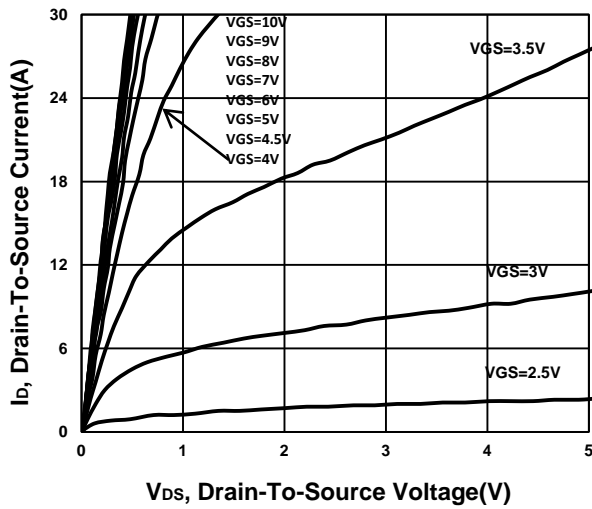
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	25			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 6.8A		19.8	25	mΩ
		V _{GS} = 10V, I _D = 7.5A		16.8	19	
Forward Transconductance ¹	g _{fs}	V _{DS} = 10V, I _D = 7.5A		22		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz	416	520	624	pF
Output Capacitance	C _{oss}		42	70	105	
Reverse Transfer Capacitance	C _{rss}		36	61	91.5	
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	0.2	2.4	4.8	Ω
Total Gate Charge ²	Q _{g(VGS=10V)}	V _{DS} = 15V, I _D = 7.5A	11	14	16.8	nC
	Q _{g(VGS=4.5V)}		6	7.8	9.4	
Gate-Source Charge ²	Q _{gs}		1.6	2	2.4	
Gate-Drain Charge ²	Q _{gd}		2.2	3.6	5	
Turn-On Delay Time ²	t _{d(on)}			14		
Rise Time ²	t _r	V _{DD} = 15V		10		
Turn-Off Delay Time ²	t _{d(off)}	I _D ≅ 7.5A, V _{GEN} = 10V, R _G = 6Ω		30		
Fall Time ²	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current ³	I _S				21	A
Forward Voltage ¹	V _{SD}	I _F = 7.5A, V _{GS} = 0V			1	V
Reverse Recovery Time	t _{rr}	I _F = 7.5A, di _F /dt = 100A / μS		12		nS
Reverse Recovery Charge	Q _{rr}			3		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

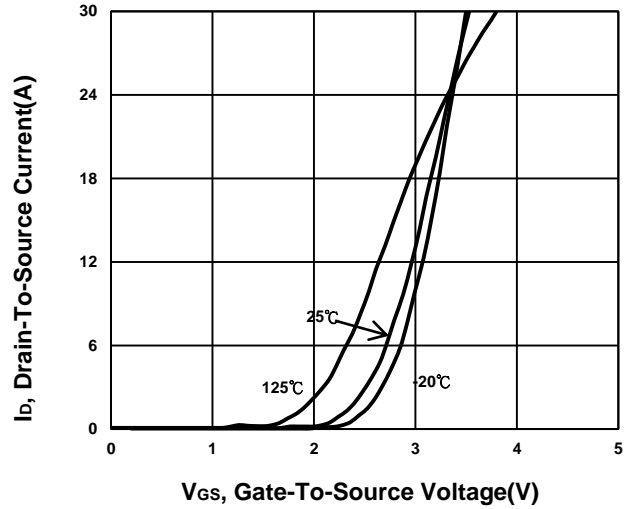
²Independent of operating temperature.

³Package limitation current is 9A.

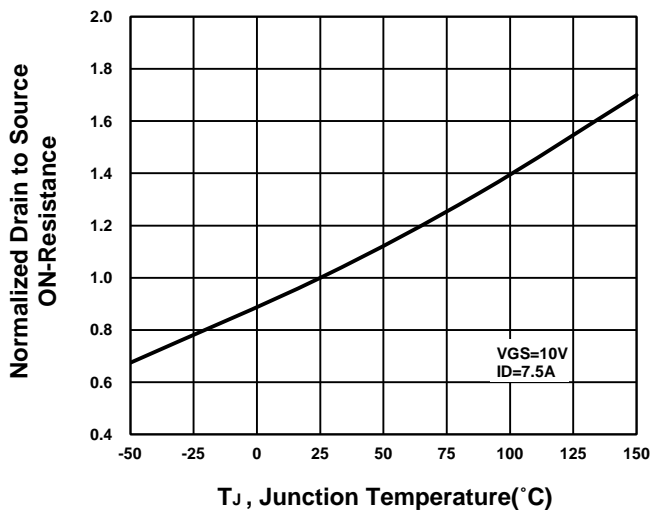
Output Characteristics



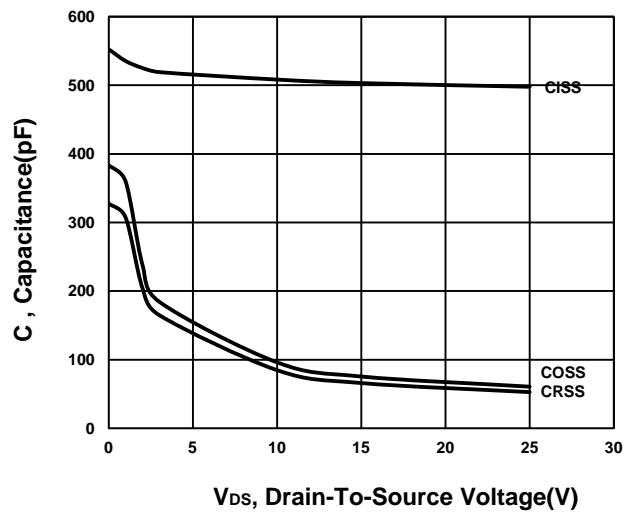
Transfer Characteristics



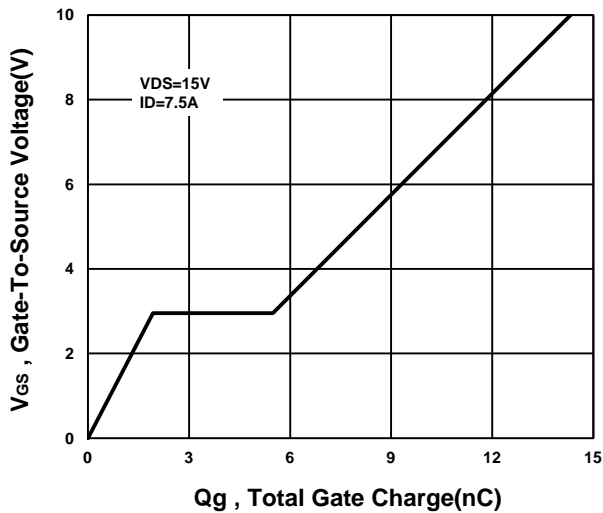
On-Resistance VS Temperature



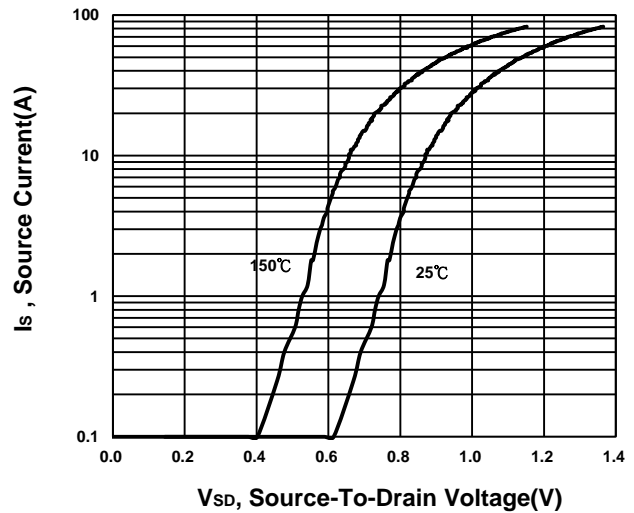
Capacitance Characteristic



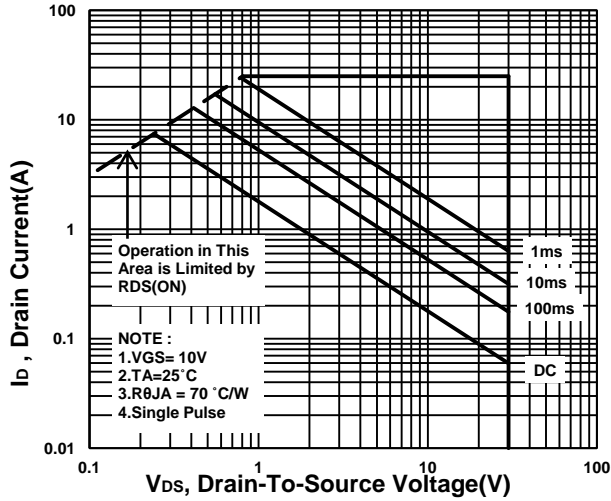
Gate charge Characteristics



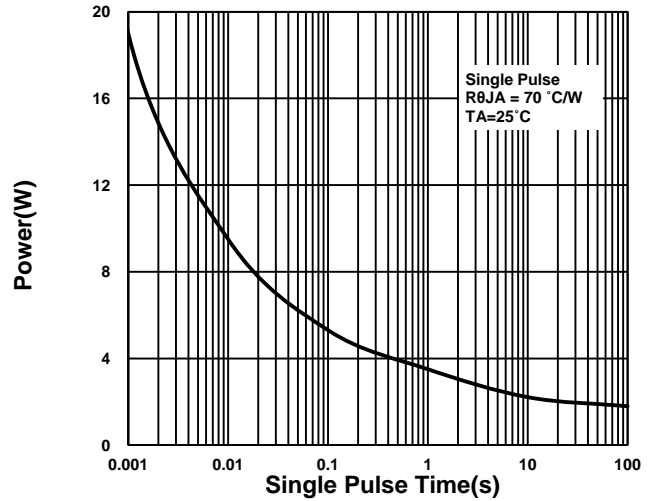
Source-Drain Diode Forward Voltage



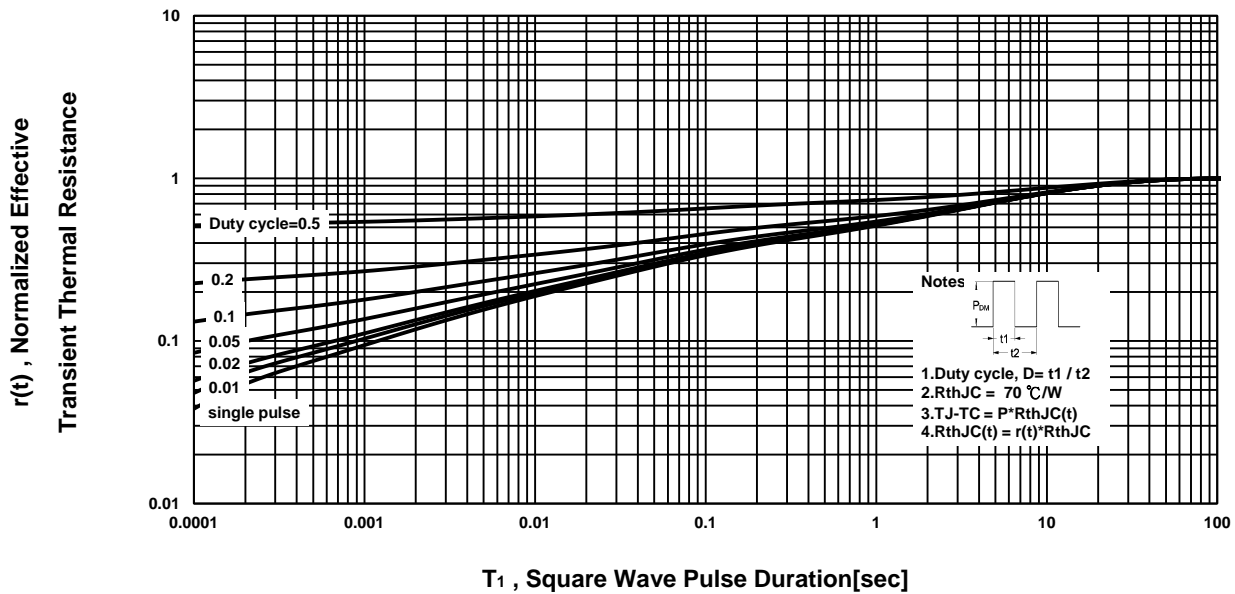
Safe Operating Area



Single Pulse Maximum Power Dissipation



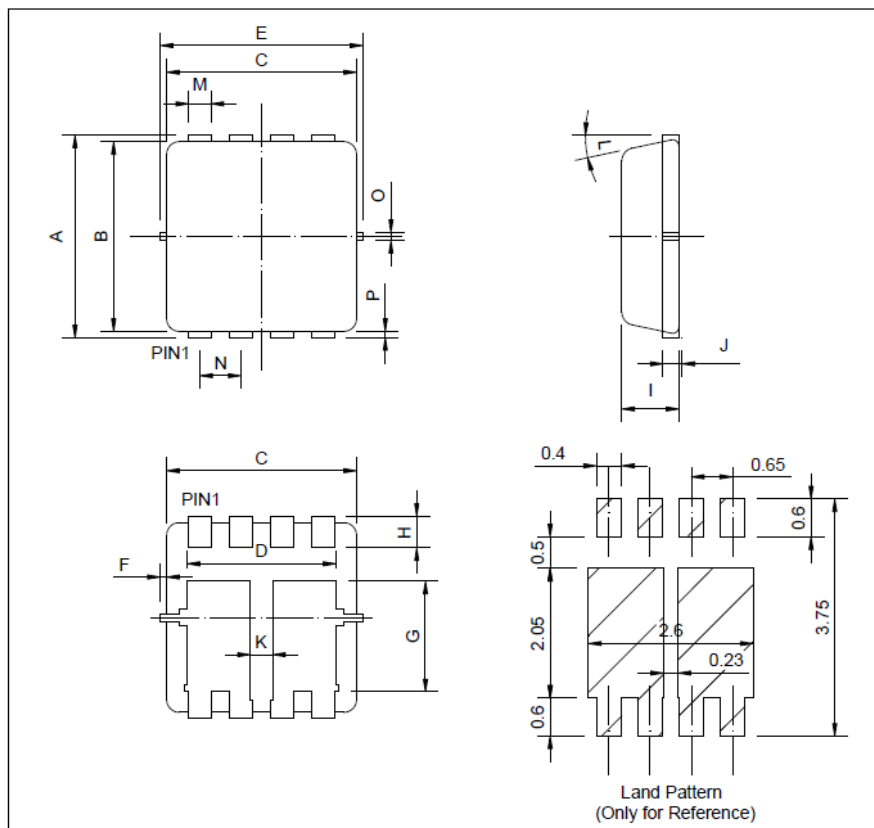
Transient Thermal Response Curve



Package Dimension

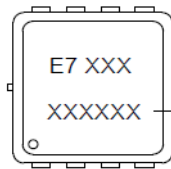
PDFN 3x3P(Dual) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3.2	3.3	3.4	I	0.7	0.75	0.8
B	2.95	3.05	3.15	J	0.1	0.15	0.25
C	2.95	3.05	3.15	K	0.35		
D		2.29		L	0°	10°	12°
E	3.2	3.3	3.4	M	0.27	0.32	0.37
F		0.13		N		0.65	
G	1.7	1.83	1.96	O		0.2	
H	0.3	0.4	0.5	P	0.06	0.13	0.2



A. Marking Information:(Please see the corresponding data sheet)

1.零件Marking 文字面說明



Lot.No(上下排相加共9碼)

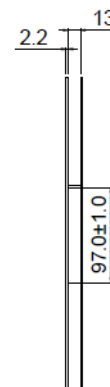
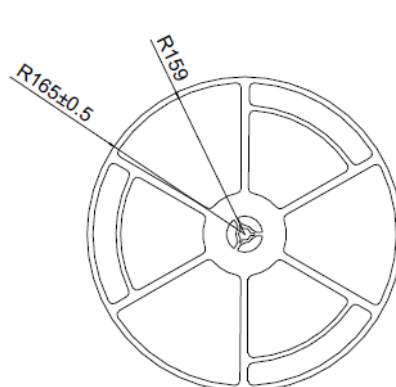
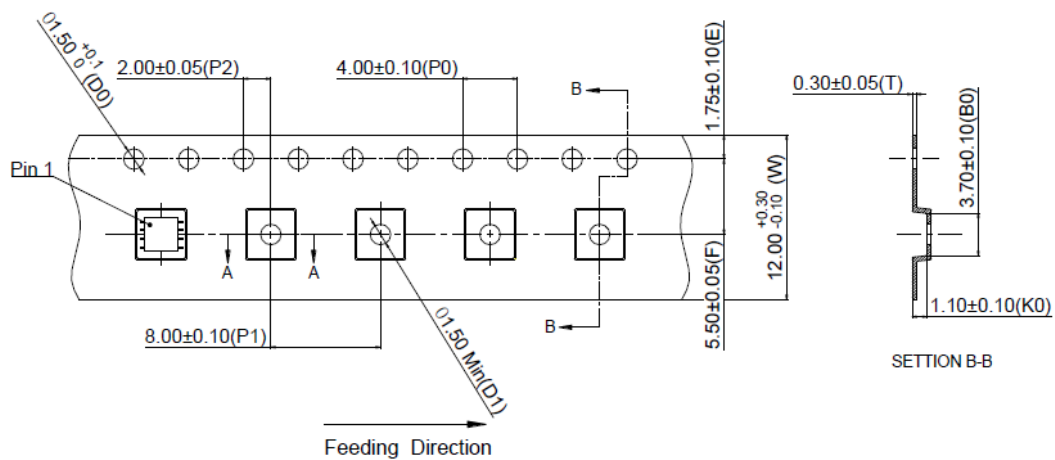
E7 : PE532DX

2.零件 Part number 說明

P E 532 D X

- Version
- D : Dual
- Device Name
- E : PDFN 3x3P
- Power MOSFET

B. Tape&Reel Information: 5000pcs/Reel

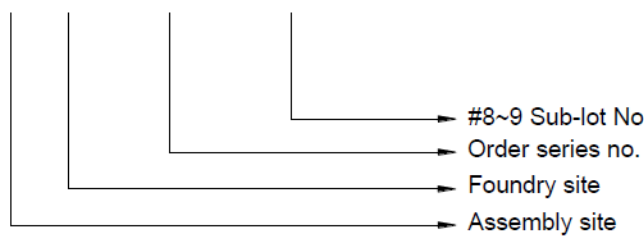


附註:All Dimension in millimeter

C. Lot.No. & Date Code rule

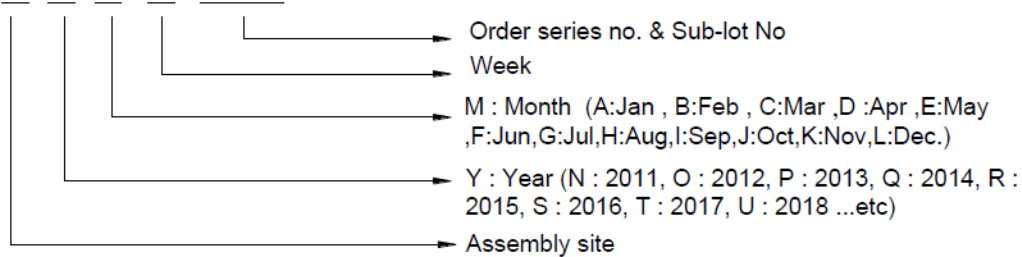
1.LOT.NO.

M N 15M21 03



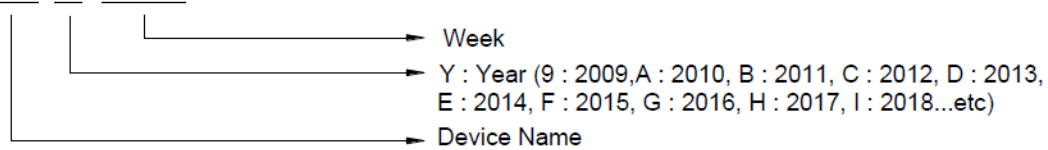
2.Date Code

D Y M X XXX



3.Date Code (for Small package)



XX Y WW



D. Label rule

標籤內容 (Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可區分英文”O”和數字”0”，”G 和”Q”的字型即可) (Or any font capable of being distinguished for Letter O and digital 0, and for G and Q))
3	NIKO-SEM	Height: 4 mm
4	NIKO SEMICONDUCTOR CO., LTD.	Height: 1 mm
5	Package	Height: 2 mm
6	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
7	Device	Height: 3 mm (Max: 16 Digit) Device Name not including Rev.
8	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
9	D/C	Height: 3 mm (Max: 7 Digit)
10	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
11	Pb Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Halogen Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
13	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least